IEEE EDS Kansai Chapter Awards 2011

■ IEEE EDS Kansai Chapter of the Year Award

Authors: **H. Umeda**
Title: "Blocking-Voltage Boosting Technology for GaN Transistors by Widening Depletion Layer in Si Substrates"
Coauthors: A. Suzuki, Y. Anda, M. Ishida, T. Ueda, T. Tanaka, D. Ueda
Affiliation: Panasonic Corp.

■ IEEE EDS Kansai Chapter MFSK Award

Authors: **H. Tomita**[1]
Title: "High speed spin-transfer switching in GMR nanopillars with perpendicular anisotropy"
Coauthors: T. Nozaki[1], T. Seki[1], T. Nagase[2], E. Kitagawa[2], M. Yoshikawa[2], T. Daibou[2], M. Nagamine[2], S. Ikegawa[2], N. Shimomura[2], H. Yoda[2], and Y. Suzuki[1]
Affiliation: [1] Osaka Univ., [2] Toshiba

Authors: **N. Morioka**
Title: "Tight-Binding Study of Size and Geometric Effects on Hole Effective Mass of Silicon Nanowires"
Coauthors: H. Yoshioka, J. Suda, and T. Kimoto
Affiliation: Kyoto Univ.

■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Authors: **Y. Yamamoto, T. Yamaguchi, Y. Kawasaki, S. Kudo, J. Tsuchimoto, K. Sato, Y. Nishida, T. Yamashita, H. Oda, and Y. Inou**e Paper ID: B-1
Title: "Performance Improvement of Metal-Gate/High-k CMOS by NiPt-Silicidation Using Laser Annealing"
Affiliation: Renesas Electronics Corporation

■ IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: **Shimpei Ogiwara** Paper ID: PA-11
Title: "High-quality Single-crystal SiGe Layers on Insulator Formed by Rapid Melt Growth"
Coauthors: Y. Suzuki, C. Yoshimoto, T. Hosoi, T. Shimura, H. Watanabe
Affiliation: Osaka University

Author: **Yumi Kawamura**[1] Paper ID: PB-5
Title: "Low Temperature Processed ZnO Thin Film Transistors Fabricated by Plasma Assisted Atomic Layer Deposition"
Coauthors: M. Tani[1], M. Horita[1,2], Y. Ishikawa[1,2], Y. Uraoka[1,2]
Affiliation: [1]Nara Institute of Science and Technology, [2]CREST

Author: **Tomohiro Higaki** Paper ID: PB-9
Title: "Flexible Zinc Oxide Thin-Film Transistors using Oxide Buffer Layers on Polyethylene Napthalate Substrates"

Coauthors: T. Tachibana, Y. Kimura, T. Maemoto, S. Sasa, M. Inoue
Affiliation: Osaka Institute of Technology

Author: **Yasuhiro Kakihara[1,2]** Paper ID: PC-3
Title: "Application of Endohedral Iron-oxide Ferritin to Resistive Memory"
Coauthors: M. Uenuma[1,2], N. Okamoto[1], K. Kawano[1,2], B. Zheng[1,2], Y. Ishikawa[1,2], I. Yamashita[1,2], Y. Uraoka[1,2]
Affiliation: [1]Nara Institute of Science and Technology, [2]CREST

Author: **Toshifumi Ota** Paper ID: PC-10
Title: "Characterization of Transient Drain Current Overshoot in Poly-Si TFTs"
Coauthors: Y. Kamakura, K. Taniguchi
Affiliation: Osaka University